

Talks and Conference Contributions

- [1] P. Brückner and F. Scholz, "Self-separation of GaN using in-situ deposited SiN as separation layer", *Int. Workshop on Nitride Semiconductors*, Kyoto, Japan, Oct. 2006.
- [2] P. Brückner and F. Scholz, "Erzeugung von freistehenden GaN-Substraten mit Hilfe von SiN-Zwischenschichten", *DGKK-Workshop III-V-Epitaxie*, Ulm, Germany, Dec. 2006.
- [3] A. Gadallah, M. Stach, F. Rinaldi, S. Lorch, I. Kardosh, P. Gerlach, and R. Michalzik, "Fabrication and characterization of GaAs-based transceiver chips for bidirectional optical data transmission", *XXVI Conf. on Solid State Physics and Materials Science* of the Egyptian Materials Research Society, *Eg-MRS 2006 & Workshop on Nanostuctures: Science, Fabrication, Characterization and Devices*, Alexandria, Egypt, Sept. 2006.
- [4] P. Gerlach, M. Peschke, T. Wenger, B.K. Saravanan, C. Hanke, S. Lorch, and R. Michalzik, "Complex coupled distributed feedback laser monolithically integrated with electroabsorption modulator and semiconductor optical amplifier at $1.3\text{ }\mu\text{m}$ wavelength", *SPIE Photonics Europe, Conf. on Integrated Optics, Silicon Photonics, and Photonic Integrated Circuits*, Strasbourg, France, Apr. 2006.
- [5] P. Gerlach and R. Michalzik, "A simple half-duplex optical link using identical Fabry–Perot lasers at $1.5\text{ }\mu\text{m}$ wavelength", Poster at Workshop *Electrical and Electronic Engineering for Communication, EEEfCOM 2006*. Ulm, Germany, June 2006.
- [6] J. Hertkorn, P. Brückner, T. Wunderer, S.B. Thapa, and F. Scholz, "AlN-Nukleation auf Saphir-Substraten für das Wachstum von hochqualitativen GaN-Schichten", *DGKK-Workshop III-V-Epitaxie*, Ulm, Germany, Dec. 2006.
- [7] A. Kroner, J.F. May, I. Kardosh, F. Rinaldi, H. Roscher, and R. Michalzik, "Novel concepts of vertical-cavity laser-based optical traps for biomedical applications", *SPIE Photonics Europe, Conf. on Biophotonics and New Therapy Frontiers*, Strasbourg, France, Apr. 2006.
- [8] A. Kroner, A. Gadallah, I. Kardosh, F. Rinaldi, and R. Michalzik, "Integrated VCSEL trap arrays for microfluidic particle separation and sorting", *EOS Topical Meeting on Biophotonics and Biomedical Optics*, Paris, France, Oct. 2006.
- [9] R. Michalzik, "Ultra-compact optical traps based on vertical-cavity laser diodes", National Physical Laboratory (NPL), New Delhi, India, Dec. 2006.
- [10] R. Michalzik, "Vertical-cavity laser diode research at Ulm University", Indian Institute of Technology Delhi, Physics Dept., New Delhi, India, Dec. 2006.
- [11] R. Michalzik, "High-performance vertical-cavity laser diodes enabling new applications" (invited), *Eighth International Conf. on Optoelectronics, Fiber Optics and Photonics, Photonics 2006*, Hyderabad, India, Dec. 2006.

- [12] R. Michalzik and A. Kroner, "Ultra-compact optical traps" (in German: "Ultra-kompakte optische Fallen"), Working Group *Medicine and Biotechnology* within the Photonics BW Association, Roche Diagnostics GmbH, Mannheim, Germany, March 2006.
- [13] R. Michalzik, "Vertical-cavity laser diodes: current research topics and applications" (in German: "Vertikallaserdioden: aktuelle Forschungsgebiete und Anwendungen"), Graduiertenkolleg 384 of the German Research Foundation (DFG): *Nanoelectronics, Micromechanics and Microoptics: Analysis and Synthesis by Ions, Electrons and Photons*, Ruhr-Universität Bochum, Bochum, Germany, Febr. 2006.
- [14] R. Michalzik, "Novel short-wavelength vertical-cavity laser diode designs and applications", *Physics Seminar* of the University of Neuchâtel, Neuchâtel, Switzerland, Jan. 2006.
- [15] B. Neubert, T. Wunderer, P. Brückner, F. Scholz, M. Feneberg, F. Lipski, M. Schirra, and K. Thonke, "Semipolar GaN/GaInN LEDs with more than 1 mW optical output power", *Int. Conf. on MOVPE*, Miyazaki, Japan, May 2006.
- [16] B. Neubert, "Research on GaN at Optoelectronics Department", *Meijo University*, Nagoya, Japan, June 2006.
- [17] J.M. Ostermann, P. Debernardi, and R. Michalzik, "Optimization of polarization-stable single- and multi-mode surface grating VCSELs towards high fabrication tolerance and superior performance", *SPIE Photonics Europe*, Conf. on *Semiconductor Lasers and Laser Dynamics II*, Strasbourg, France, Apr. 2006.
- [18] M.C. Riedl, F. Rinaldi, S. Menzel, F. Demaria, S. Lorch, I. Kardosh, R. Rösch, R. Michalzik, and P. Unger, "Spannungskompensation für Halbleiter-Scheibenlaser und VCSEL", *DGKK-Workshop III-V-Epitaxie*, Ulm, Germany, Dec. 2006.
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- [23] F. Scholz, “GaN für die Optoelektronik: Herausforderungen und Chancen zur Effizienz-Steigerung von Lichtemittern”, *TU Karlsruhe*, Karlsruhe, Germany, Febr. 2006.
- [24] F. Scholz, “Selektive Epitaxie von GaN: Bessere Wafer, hellere LEDs?”, *TU Ilmenau*, Ilmenau, Germany, Febr. 2006.
- [25] F. Scholz, “Piezoreduzierte Quantenfilme auf selektiv gewachsenen GaN-Streifen: Chancen für grüne Laser?”, *DFG-Rundgespräch*, Regensburg, March 2006.
- [26] F. Scholz, “Nitride activities at Optoelectronics Dept.”, *NTT Basic Research Lab*, Atsugi, Japan, May 2006.
- [27] F. Scholz, “Nitride activities at Optoelectronics Dept.”, *Tokyo University of Agriculture and Technology*, Tokyo, Japan, May 2006.
- [28] M. Stach, M. Chandran, F. Rinaldi, S. Lorch, I. Kardosh, H. Roscher, P. Gerlach, and R. Michalzik, “Monolithically integrated transceiver chips for bidirectional optical interconnection”, *SPIE Photonics Europe, Conf. on Micro-Optics, VCSELs, and Photonic Interconnects II: Fabrication, Packaging, and Integration*, Strasbourg, France, Apr. 2006.
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- [32] M. Stach, F. Rinaldi, S. Lorch, and R. Michalzik, “Novel optoelectronic components for bidirectional optical Gbit/s computer networks” (in German: “Neuartige optoelektronische Komponenten für bidirektionale optische Gbit/s-Computer-Netzwerke”), *9th Workshop on Optics in Computing Technology, ORT 2006*, Siegen, Germany, Oct. 2006.

- [33] M. Stach, F. Rinaldi, S. Lorch, and R. Michalzik, “Gbit/s-range bidirectional optical data transmission at 850 nm wavelength for automotive and in-house networks based on novel transceiver chips and PCS or graded-index glass fibers” (in German: “Bidirektionale optische Datenübertragung im Gbit/s-Bereich bei 850 nm Wellenlänge für Automotive- und Inhaus-Netze basierend auf neuartigen Transceiver-Bauelementen sowie PCS-Fasern oder Gradientenindex-Glasfasern”), *13th ITG Symposium on Communication Cable Networks*, Köln, Germany, Dec. 2006.
- [34] S.B. Thapa, C. Kirchner, F. Scholz, G.M. Prinz, K. Thonke, R. Sauer, A. Chuvilin, J. Biskupek, U. Kaiser, and D. Hofstetter, “Structural and spectroscopic properties of AlN grown by MOVPE”, Poster at *Int. Conf. on MOVPE*, Miyazaki, Japan, May 2006.
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